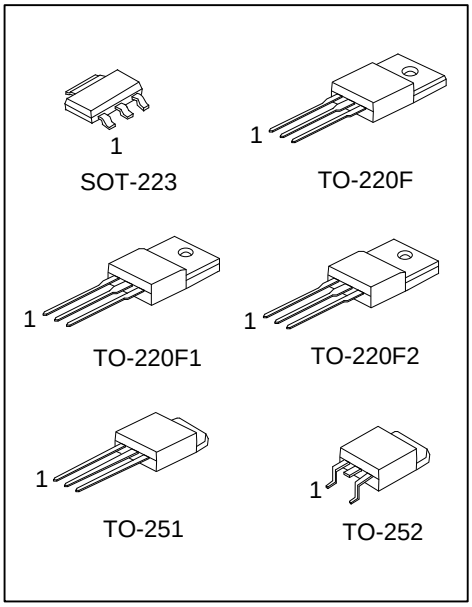
2N60-TC

Power MOSFET

2A, 600V N-CHANNEL POWER MOSFET



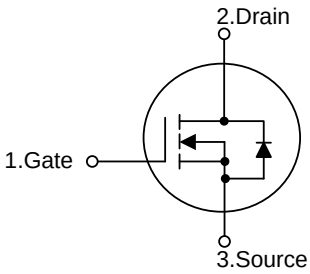
■ DESCRIPTION

The UTC **2N60-TC** is a high voltage power MOSFET and is designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and have a high rugged avalanche characteristics. This power MOSFET is usually used at high speed switching applications in power supplies, PWM motor controls, high efficient AC to DC converters and bridge circuits.

■ FEATURES

* $R_{DS(ON)} \leq 4.2\ \Omega$ @ V_{GS}=10V, I_D=1.0A
* High Switching Speed

■ SYMBOL



■ ORDERING INFORMATION

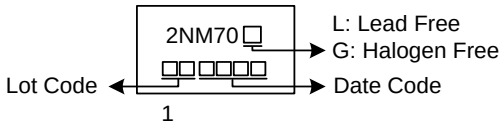
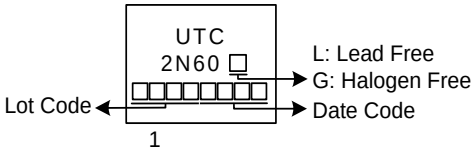
Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
2N60L-AA3-R	2N60G-AA3-R	SOT-223	G	D	S	Tape Reel
2N60L-TF1-T	2N60G-TF1-T	TO-220F1	G	D	S	Tube
2N60L-TF2-T	2N60G-TF2-T	TO-220F2	G	D	S	Tube
2N60L-TF3-T	2N60G-TF3-T	TO-220F	G	D	S	Tube
2N60L-TM3-T	2N60G-TM3-T	TO-251	G	D	S	Tube
2N60L-TN3-R	2N60G-TN3-R	TO-252	G	D	S	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source

2N60G-AA3-R
(1)Packing Type
(2)Package Type
(3)Green Package

(1) R: Tape Reel, T: Tube
(2) AA3: SOT-223, TF3: TO-220F, TF1: TO-220F1
TF2: TO-220F2, TM3: TO-251, TN3: TO-252
(3) G: Halogen Free and Lead Free, L: Lead Free

■ MARKING

SOT-223	TO-220F / TO-220F1 / TO-220F2 / TO-251 / TO-252
	

■ ABSOLUTE MAXIMUM RATINGS (T_C = 25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	600	V
Gate-Source Voltage		V_{GSS}	± 30	V
Drain Current	Continuous	I_D	2	A
	Pulsed (Note 2)	I_{DM}	4	A
Avalanche Energy	Single Pulsed (Note 3)	E_{AS}	80	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	4.3	V/ns
Power Dissipation	SOT-223	P_D	2.5	W
	TO-220F/TO-220F1 TO-220F2		23	W
	TO-251/TO-252		44	W
Junction Temperature		T_J	+150	°C
Storage Temperature		T_{STG}	-55 ~ +150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.
2. Repetitive Rating: Pulse width limited by maximum junction temperature.
3. L = 10mH, I_{AS} = 4.0A, V_{DD} = 50V, R_G = 25 Ω Starting T_J = 25°C
4. I_{SD} ≤ 2.0A, di/dt ≤200A/μs, V_{DD} ≤BV_{DSS}, Starting T_J = 25°C

■ THERMAL DATA

PARAMETER		SYMBOL	RATING	UNIT
Junction to Ambient	SOT-223	θ_{JA}	160	°C/W
	TO-220F/TO-220F1 TO-220F2		62.5	°C/W
	TO-251/TO-252		100	°C/W
Junction to Case	SOT-223	θ_{JC}	50 (Note)	°C/W
	TO-220F/TO-220F1 TO-220F2		5.5	°C/W
	TO-251/TO-252		2.87 (Note)	°C/W

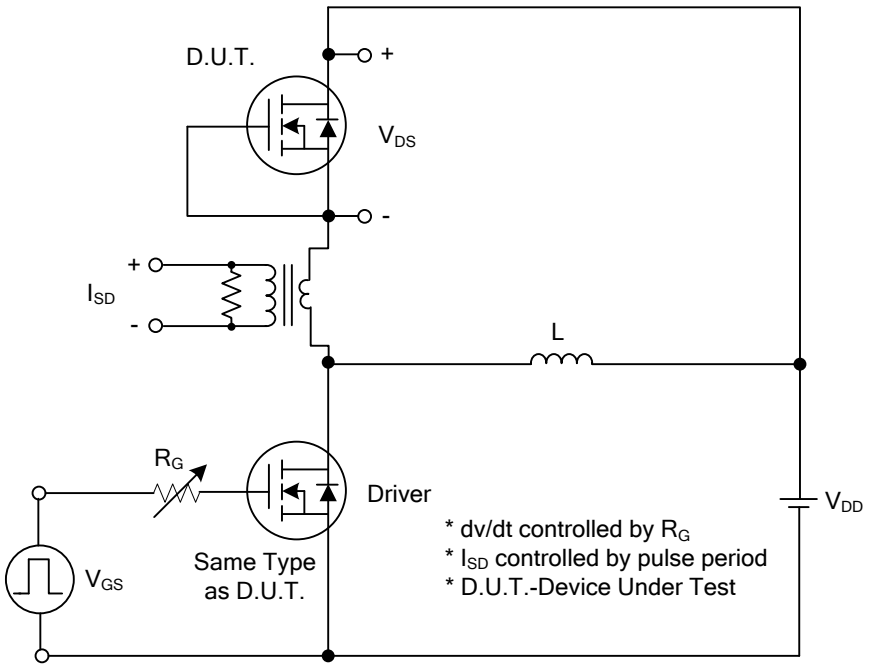
Note: Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

■ ELECTRICAL CHARACTERISTICS (T_J = 25°C, unless otherwise specified)

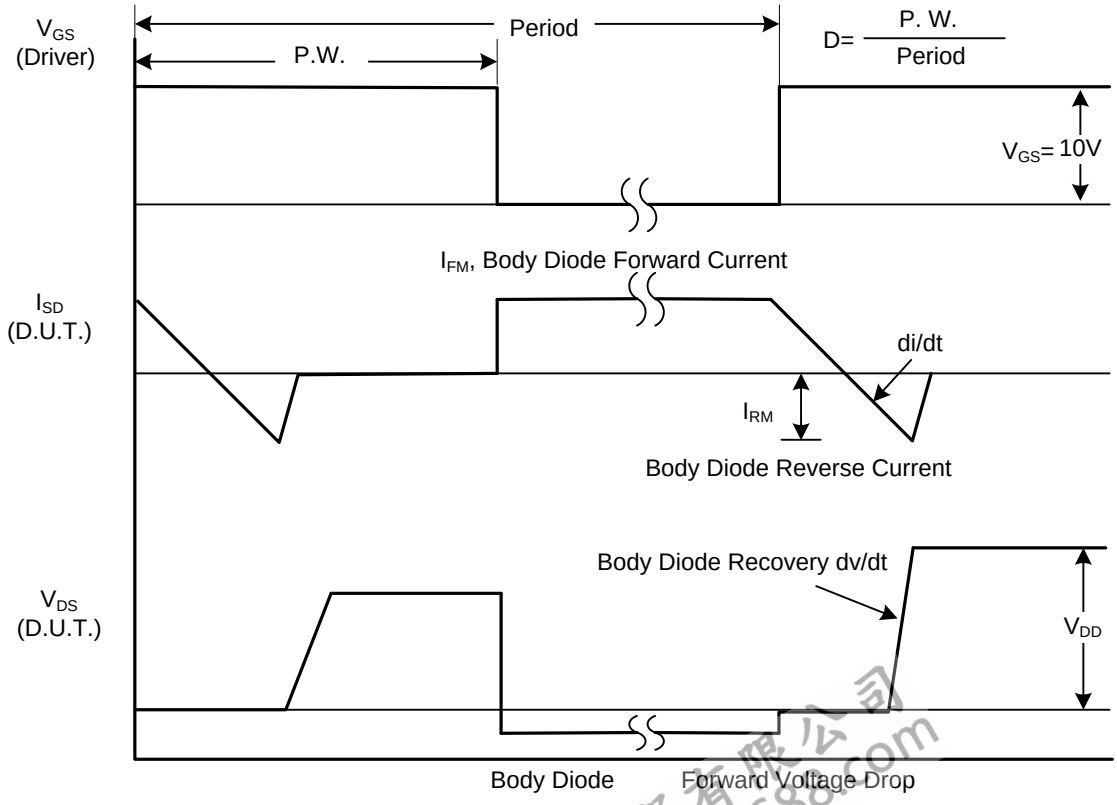
PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage		BV_{DSS}	V_{GS}=0V, I_D= 250μA	600			V
Drain-Source Leakage Current		I_{DSS}	V_{DS}=600V, V_{GS}=0V			10	μA
Gate-Source Leakage Current	Forward	I_{GSS}	V_{GS}=30V, V_{DS}=0V			100	nA
	Reverse		V_{GS}=-30V, V_{DS}=0V			-100	nA
ON CHARACTERISTICS							
Gate Threshold Voltage		$V_{GS(TH)}$	V_{DS}=V_{GS}, I_D=250μA	2.0		4.0	V
Static Drain-Source On-State Resistance		$R_{DS(ON)}$	V_{GS}=10V, I_D=1.0A			4.2	Ω
DYNAMIC CHARACTERISTICS							
Input Capacitance		C_{ISS}	V_{GS}=0V, V_{DS}=25V, f=1.0 MHz		300		pF
Output Capacitance		C_{OSS}			40		pF
Reverse Transfer Capacitance		C_{RSS}			2.5		pF
SWITCHING CHARACTERISTICS							
Total Gate Charge (Note 1)		Q_G	V_{DS}=100V, V_{GS}=10V, I_D=1.0A I_G=1mA (Note 1, 2)		8.6		nC
Gateource Charge		Q_{GS}			4		nC
Gate-Drain Charge		Q_{GD}			1.5		nC
Turn-on Delay Time (Note 1)		$t_{D(ON)}$	V_{DS}=300V, V_{GS}=10V, I_D=2.0A, R_G=25Ω (Note 1, 2)		5		ns
Rise Time		t_R			17		ns
Turn-off Delay Time		$t_{D(OFF)}$			20		ns
Fall-Time		t_F			20		ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS							
Maximum Body-Diode Continuous Current		I_S				2	A
Maximum Body-Diode Pulsed Current		I_{SM}				8	A
Drain-Source Diode Forward Voltage (Note 1)		V_{SD}	V_{GS}=0V, I_S=2.0A			1.4	V
Reverse Recovery Time (Note 1)		t_{rr}	V_{GS}=0V, I_S=2.0A, dI_F/dt=100A/μs (Note1)		216		ns
Reverse Recovery Charge		Q_{rr}			1.1		μC

Notes: 1. Pulse Test : Pulse width ≤ 300μs, Duty cycle ≤ 2%.
2. Essentially independent of operating temperature.

■ TEST CIRCUITS AND WAVEFORMS

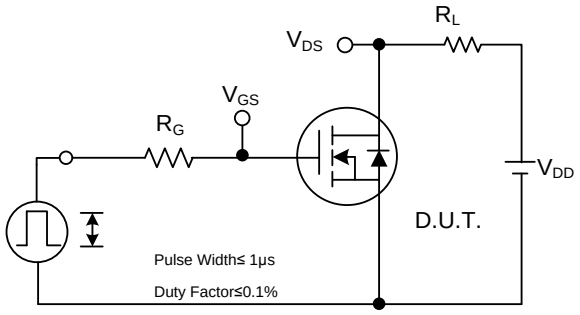


Peak Diode Recovery dv/dt Test Circuit

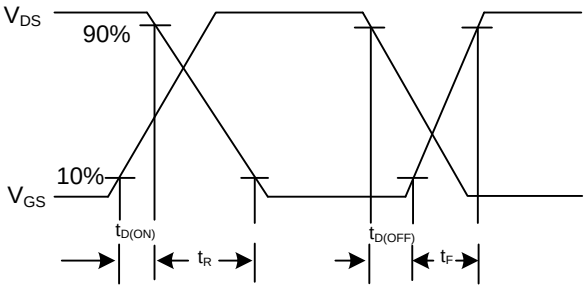


Peak Diode Recovery dv/dt Waveforms

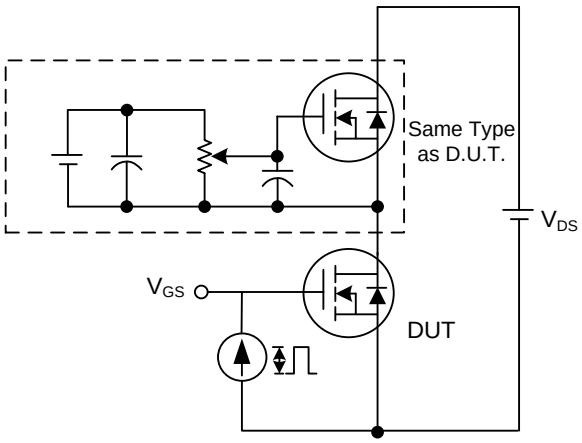
■ TEST CIRCUITS AND WAVEFORMS



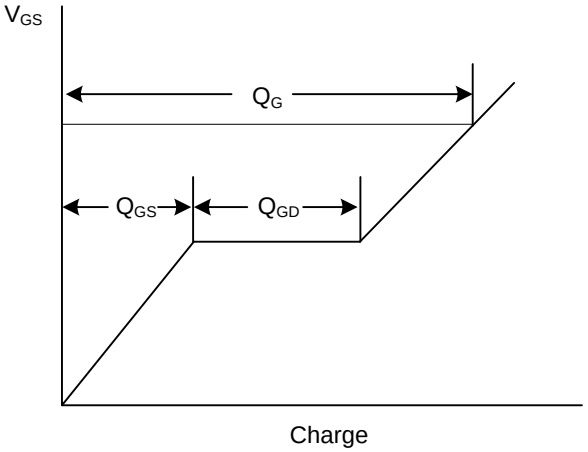
Switching Test Circuit



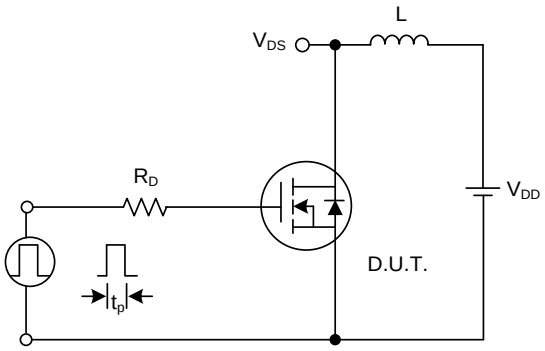
Switching Waveforms



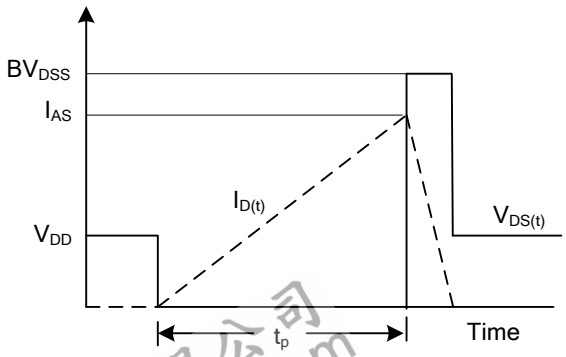
Gate Charge Test Circuit



Gate Charge Waveform



Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms

■ TYPICAL CHARACTERISTICS